

## 2<sup>nd</sup> Generation thinQ!™ SiC Schottky Diode

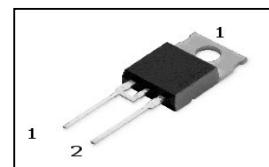
### Features

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery / No forward recovery
- No temperature influence on the switching behavior
- High surge current capability
- Pb-free lead plating; RoHs compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Breakdown voltage tested at 5mA<sup>2)</sup>

### Product Summary

$V_{DC}$	600	V
$Q_c$	12	nC
$I_F$	5	A

PG-T0220-2-2



### thinQ! 2G Diode specially designed for fast switching applications like:

- CCM PFC
- Motor Drives

Type	Package		Marking	Pin 1	Pin 2
IDT05S60C	PG-T0220-2-2		D05S60C	C	A

Maximum ratings, at  $T_j=25$  °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous forward current	$I_F$	$T_c < 140$ °C	5	A
RMS forward current	$I_{F,RMS}$	$f=50$ Hz	7.5	
Surge non-repetitive forward current, sine halfwave	$I_{F,SM}$	$T_c = 25$ °C, $t_p = 10$ ms	42	
Repetitive peak forward current	$I_{F,RM}$	$T_j = 150$ °C, $T_c = 100$ °C, $D = 0.1$	21	
Non-repetitive peak forward current	$I_{F,max}$	$T_c = 25$ °C, $t_p = 10$ µs	180	
$i^2t$ value	$\int i^2 dt$	$T_c = 25$ °C, $t_p = 10$ ms	9	A <sup>2</sup> s
Repetitive peak reverse voltage	$V_{RRM}$		600	V
Diode ruggedness dv/dt	$dv/dt$	$V_R = 0 \dots 480$ V	50	V/ns
Power dissipation	$P_{tot}$	$T_c = 25$ °C	55	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 175	°C
Mounting torque		M3 and M3.5 screws	60	Ncm

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - case	$R_{thJC}$		-	-	2.7	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	leaded	-	-	62	
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	1.6mm ( 0.063in.) from case for 10s	-	-	260	°C

**Electrical characteristics**, at  $T_j=25$  °C, unless otherwise specified

**Static characteristics**

DC blocking voltage	$V_{DC}$	$I_R=0.07$ mA	600	-	-	V
Diode forward voltage	$V_F$	$I_F=5$ A, $T_j=25$ °C	-	1.5	1.7	
		$I_F=5$ A, $T_j=150$ °C	-	1.7	2.1	
Reverse current	$I_R$	$V_R=600$ V, $T_j=25$ °C	-	0.6	70	$\mu$ A
		$V_R=600$ V, $T_j=150$ °C	-	2.5	700	

**AC characteristics**

Total capacitive charge	$Q_c$	$V_R=400$ V, $I_F \leq I_{F,max}$ , $di_F/dt=200$ A/ $\mu$ s,	-	12	-	nC
Switching time <sup>3)</sup>	$t_c$	$T_j=150$ °C	-	-	<10	ns
Total capacitance	$C$	$V_R=1$ V, $f=1$ MHz	-	240	-	pF
		$V_R=300$ V, $f=1$ MHz	-	30	-	
		$V_R=600$ V, $f=1$ MHz	-	30	-	

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> All devices tested under avalanche conditions, for a time period of 5ms, at 5mA.

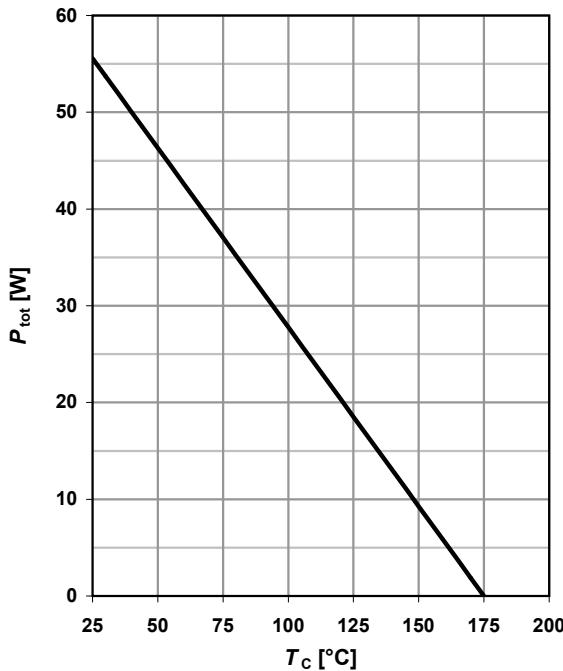
<sup>3)</sup>  $t_c$  is the time constant for the capacitive displacement current waveform (independent from  $T_j$ ,  $I_{LOAD}$  and  $di/dt$ ), different from  $t_{rr}$ , which is dependent on  $T_j$ ,  $I_{LOAD}$ ,  $di/dt$ . No reverse recovery time constant  $t_{rr}$  due to absence of minority carrier injection.

<sup>4)</sup> Only capacitive charge occurring, guaranteed by design.

**1 Power dissipation**

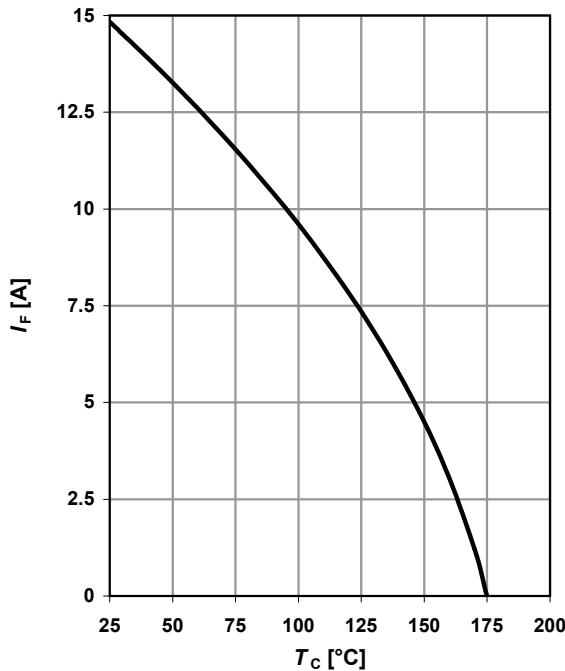
$$P_{\text{tot}} = f(T_c)$$

parameter:  $R_{\text{thJC(max)}}$


**2 Diode forward current**

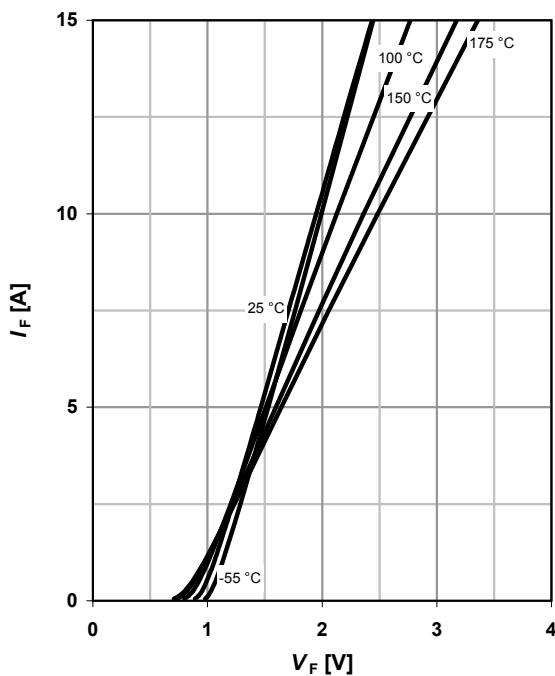
$$I_F = f(T_c); T_j \leq 175 \text{ °C}$$

parameter:  $R_{\text{thJC(max)}}$ ;  $V_{F(\text{max})}$

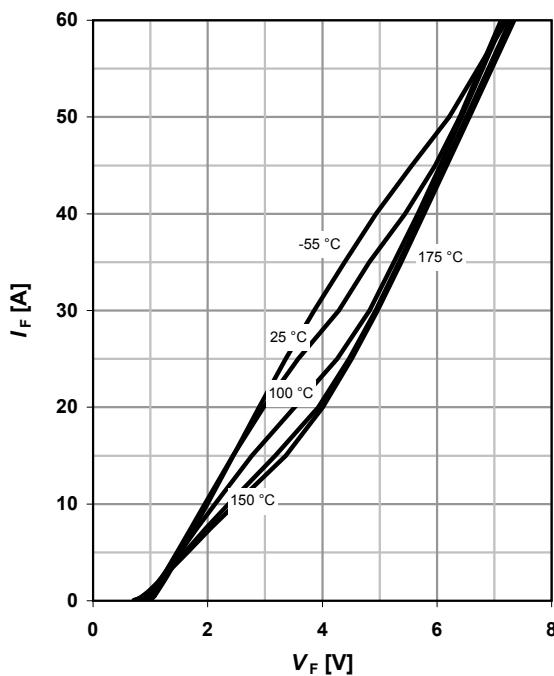

**3 Typ. forward characteristic**

$$I_F = f(V_F); t_p = 400 \mu\text{s}$$

parameter:  $T_j$

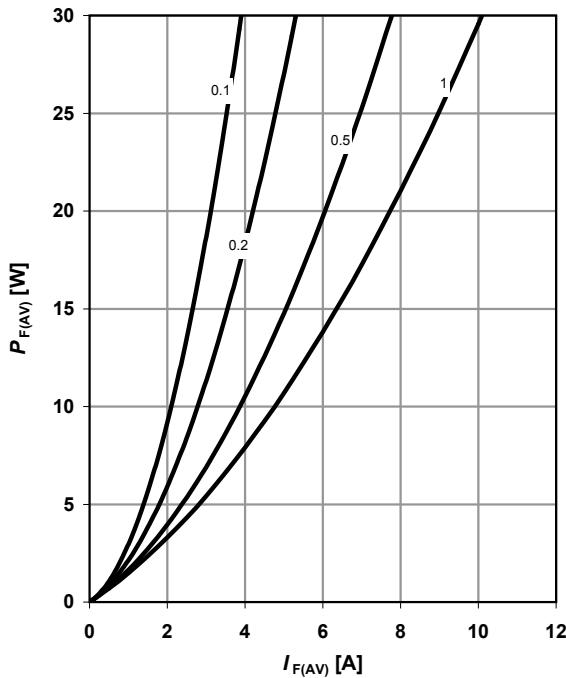

**4 Typ. forward characteristic in surge current mode**

$$I_F = f(V_F); t_p = 400 \mu\text{s}; \text{ parameter: } T_j$$



**5 Typ. forward power dissipation vs.  
average forward current**

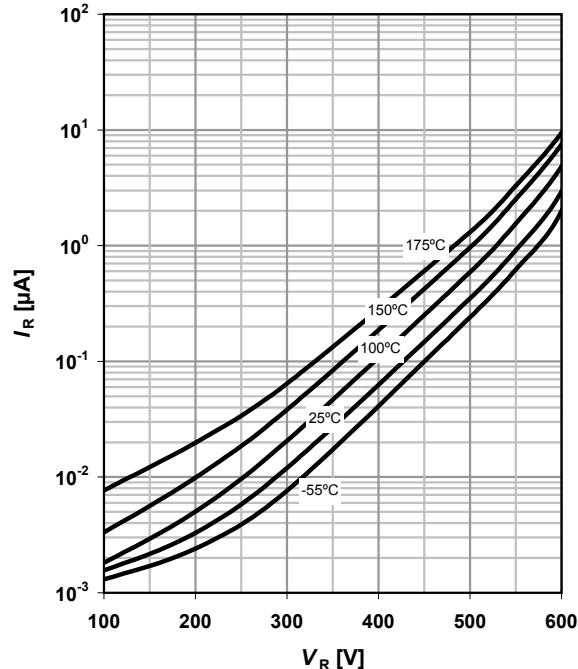
$P_{F,AV}=f(I_F)$ ,  $T_C=100\text{ }^\circ\text{C}$ , parameter:  $D=t_p/T$



**6 Typ. reverse current vs. reverse voltage**

$I_R=f(V_R)$

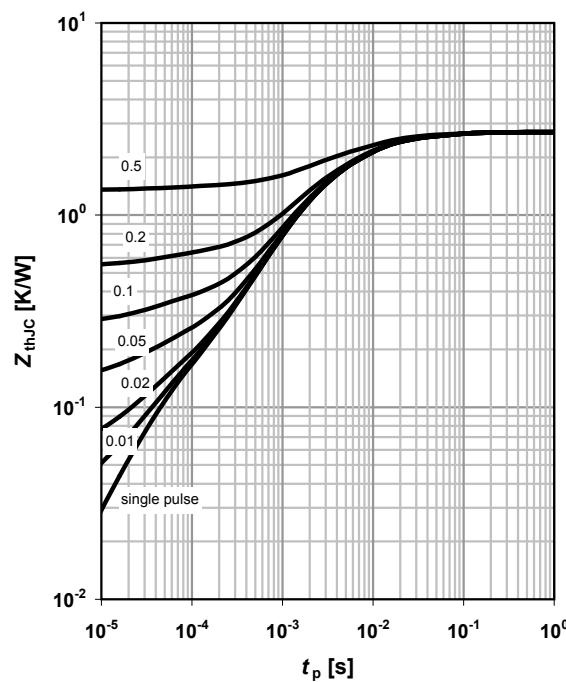
parameter:  $T_j$



**7 Transient thermal impedance**

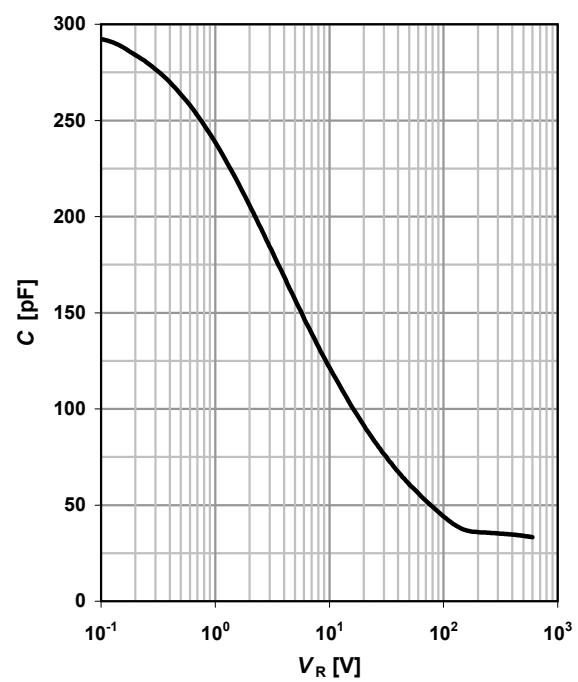
$Z_{thJC}=f(t_p)$

parameter:  $D=t_p/T$



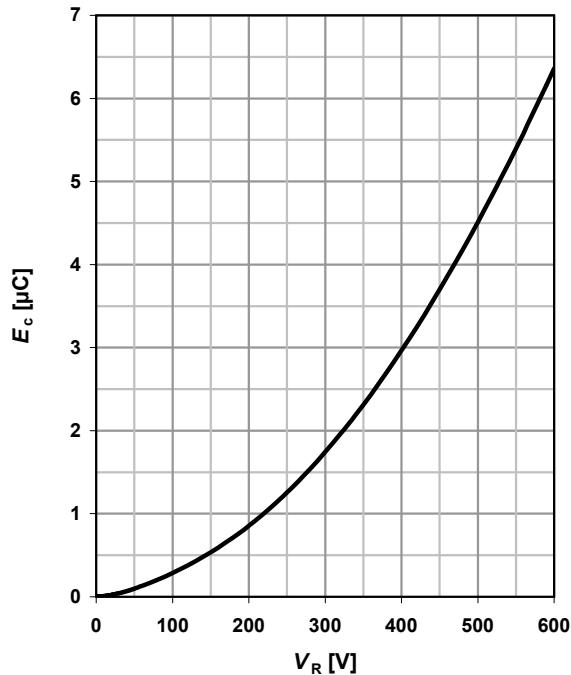
**8 Typ. capacitance vs. reverse voltage**

$C=f(V_R)$ ;  $T_C=25\text{ }^\circ\text{C}$ ,  $f=1\text{ MHz}$

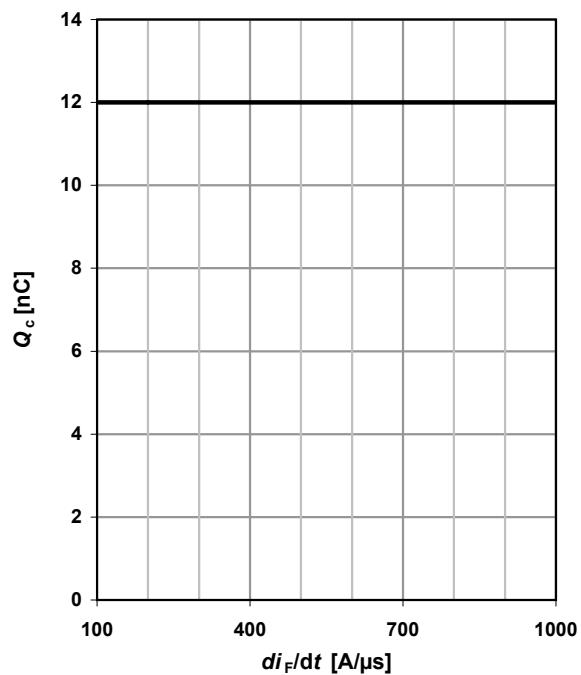


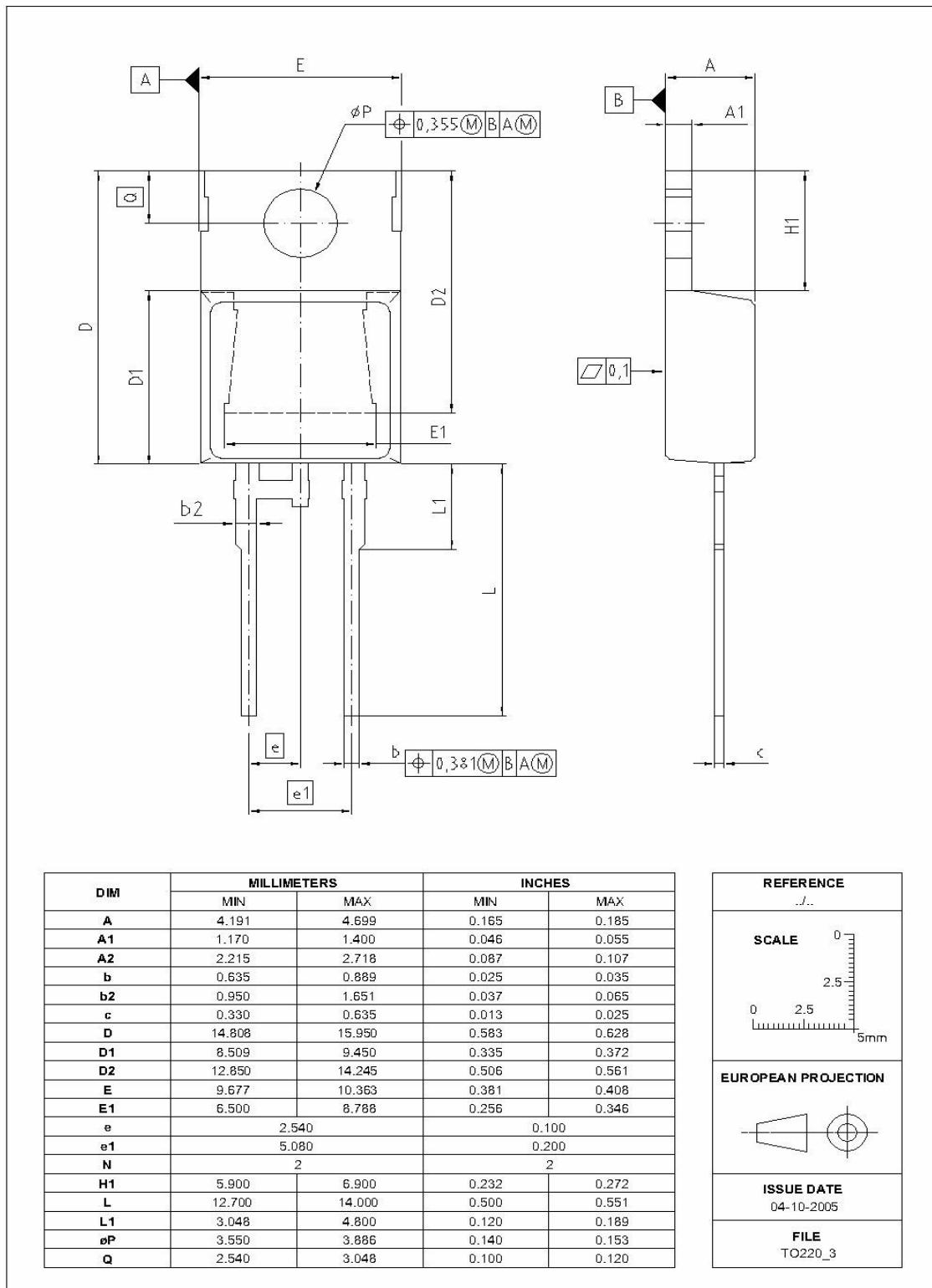
**9 Typ. C stored energy**

$$E_C = f(V_R)$$


**10 Typ. capacitance charge vs. current slope**

$$Q_C = f(di_F/dt)^{4/3}, \quad T_J = 150^\circ\text{C}; \quad I_F \leq I_{F,\text{max}}$$



**PG-TO220-2-2: Outline**


Dimensions in mm/inches

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